

IN THE CLAIMS

1. (Previously presented) An insulating nitride layer formed as a buffer layer from a group III-V nitride compound semiconductor heavily doped mostly with cadmium.

2. (Previously presented) An insulating nitride layer as defined in Claim 1, which is heavily doped substantially with said cadmium as an impurity.

3. (Canceled).

4. (Previously presented) An insulating nitride layer as defined in Claim 1, which is doped with said cadmium in an amount not less than $1 \times 10^{17}/\text{cm}^3$.

5. (Original) An insulating nitride layer as defined in Claim 1, in which said group III-V nitride compound semiconductor is GaN, AlN, InN, or BN, or a mixture thereof.

6-12. (Withdrawn).

13. (Previously presented) A semiconductor device which has an insulating nitride layer formed as a buffer layer from a group III-V nitride compound semiconductor heavily doped mostly with cadmium.

14. (Original) A semiconductor device as defined in Claim 13, in which said group III-V nitride compound semiconductor

15. (Original) A semiconductor device as defined in Claim 13, in which an active layer is formed on said insulating nitride layer.

16. (Amended) A semiconductor device as defined in Claim 13, in which the insulating nitride layer is heavily doped substantially with said cadmium as an impurity.

17. (Canceled).

18. (Amended) A semiconductor device as defined in Claim 13, in which the insulating

nitride layer is doped with said cadmium in an amount not less than $1 \times 10^{17}/\text{cm}^3$.

19. (Original) A semiconductor device as defined in claim 13 or 14, in which said group III-V nitride compound semiconductor is GaN, AlN, InN, or BN, or a mixture thereof.

20-27. (Withdrawn).